Elektronische Bauelemente

MJD32C

-3A, -100V

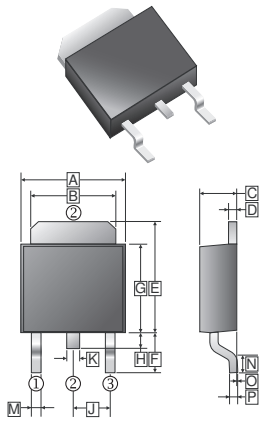
PNP Epitaxial Silicon Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

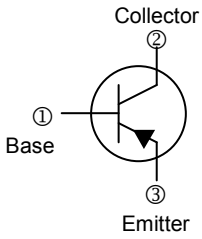
DESCRIPTION

- Designed for General Purpose Amplifier and Low Speed Switching Applications
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("–1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("T4" Suffix)
- Electrically Similar to Popular TIP31 and TIP32 Series

TO-252 (D-Pack)



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.35	6.9	J	2.3 REF.	
B	4.95	5.53	K	0.89 REF.	
C	2.1	2.5	M	0.45	1.14
D	0.41	0.9	N	1.55 Typ.	
E	6	7.5	O	0	0.13
F	2.90 REF		P	0.58 REF.	
G	5.4	6.4			
H	0.6	1.2			



PACKAGE INFORMATION

Package	MPQ	Leader Size
TO-252	2.5K	13 inch

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-3	A
Collector Power Dissipation	P_C	1.25	W
Junction and Storage Temperature	T_J, T_{STG}	150, -65 ~ 150	°C

CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit	Test Condition
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-100	-	V	I_C= -1mA, I_E=0
Collector-Emitter Breakdown Voltage [1]	$V_{CEO(sus)}$	-100	-	V	I_C= -30mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-	V	I_E= -1mA, I_C=0
Collector Cut-Off Current	I_{CES}	-	-20	uA	V_{CE}= -100V, V_{EB}=0
Collector Cut-Off Current	I_{CEO}	-	-50	uA	V_{CE}= -60V, I_B=0
Emitter Cut-Off Current	I_{EBO}	-	-1	mA	V_{EB}= -5V, I_C=0
DC Current Gain	$h_{FE(1)}$	25	-		V_{CE}= -4V, I_C= -1A
	$h_{FE(2)}$	15	75		V_{CE}= -4V, I_C= -3A
Collector-Emitter Saturation Voltage	$V_{CE(Sat)}$	-	-1.2		I_C= -3A, I_B= -0.375A
Base-Emitter Voltage	$V_{BE(Sat)}$	-	-1.8		V_{CE}= -4V, I_C= -3A
Transition Frequency	f_T	3	-	MHz	V_{CE}= -10V, I_C= -0.5A, f_T=1KHz

Notes:
1. Pulse Test: Pulse width≦300μs, duty cycle≦2%

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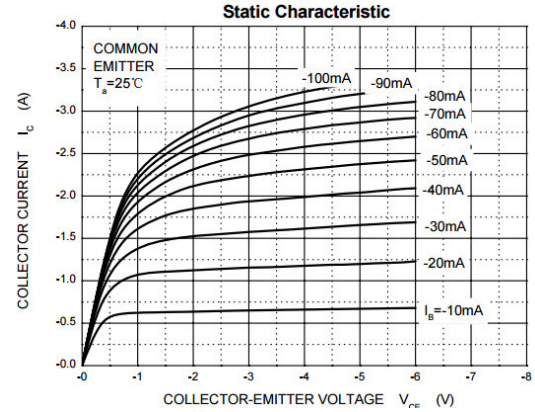
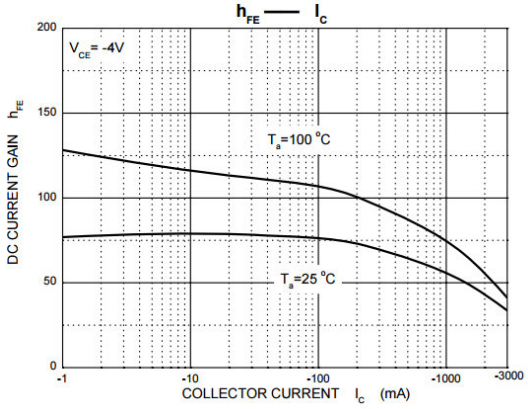
CHARACTERISTIC CURVES

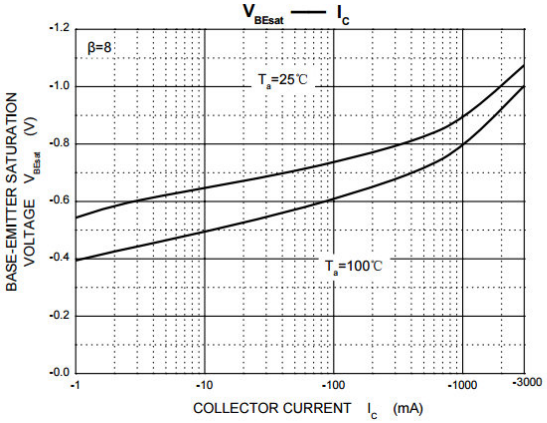
Static Characteristic



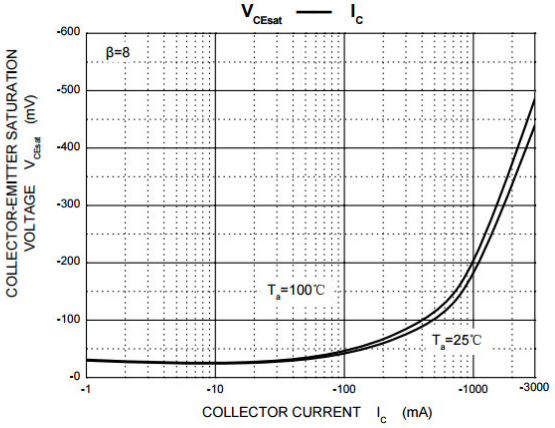
h_{FE} — I_C



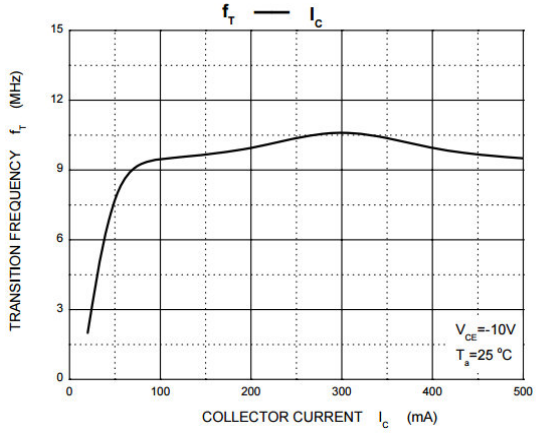
V_{BEsat} — I_C



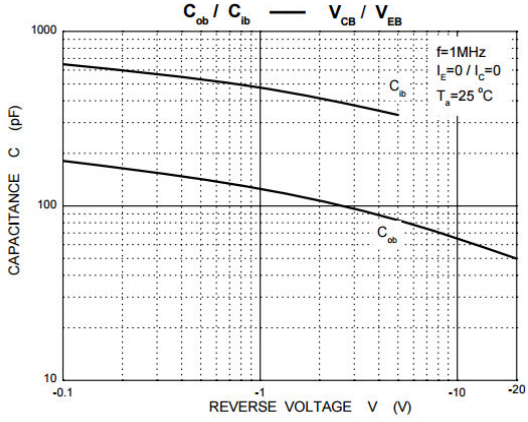
V_{CEsat} — I_C



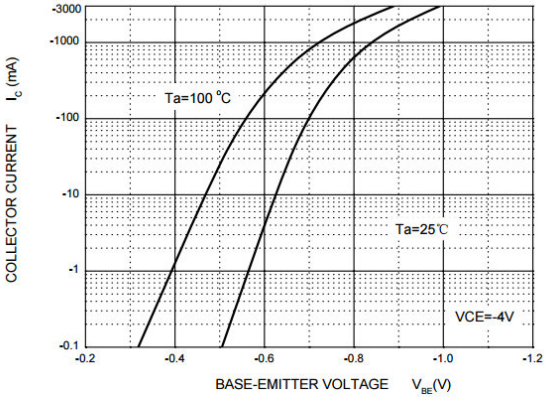
f_T — I_C



C_{ob} / C_{ib} — V_{CB} / V_{EB}



I_C — V_{BE}



P_c — T_a

